S3P6R

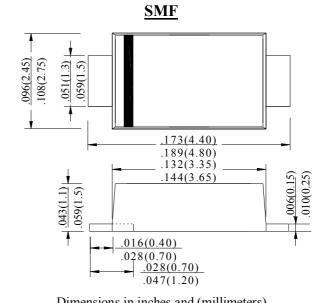
3.0AMPS. PLANAR MOS SCHOTTKY BARRIER RECTIFIERS

FEATURE

- . For surface mounted application
- . High current capability
- . Low forward voltage drop
- . Low power loss, high efficiency
- . High surge current capability
- . High temperature soldering guaranteed 260°C/10 seconds at terminals.

MECHANICAL DATA

- . Terminal: Solder plated
- . Case: Molded with UL-94 Class V-0 recognized Flame Retardant Epoxy (free halogen)
- . Polarity: color band denotes cathode
- . Packaging: 12mm tape per EIA STD RS-481



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number		SYM BOL	S3P6R	units
Maximum Recurrent Peak Reverse Voltage		$V_{ m RRM}$	60	V
Maximum RMS Voltage		$V_{ m RMS}$	42	V
Maximum DC blocking Voltage		$V_{ m DC}$	60	V
Maximum Average Forward Rectified Current at $T_L = 90^{\circ}C$		$I_{\mathrm{F(AV)}}$	3.0	A
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)		$I_{ m FSM}$	70	A
Maximum Forward Voltage	at 3.0A DC	$V_{\rm FMax}$	0.52	V
@T _A =25°C	at 1.0A DC	$V_{ m FType}$	0.37	
Maximum DC Reverse Current @T _A =25°C		7	0.2	A
at rated DC blocking voltage	@T _A =100°C	$I_{ m R}$	10	mA
Typical Junction Capacitance (Note1)		$C_{ m J}$	72	pF
Typical Thermal Resistance (Note2)		$R_{(JL)}$	45	°C/W
		$R_{(JC)}$	28	
Storage Temperature		T _{STG}	-55 to +150	°C
Operating Junction Temperature		$T_{ m J}$	-55 to +150	°C

Note:

- 1. Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc
- 2. Measured on P.C.Board with 0.2×0.2"(5.0×5.0mm)Copper Pad Areas.

RATING AND CHARACTERISTIC CURVES (S3P6R)

